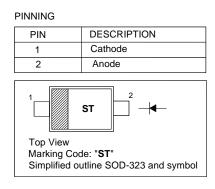
SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

Applications

• UHF Band Mixer



Absolute Maximum Ratings (T_a = 25 °C)

5 (1)			
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V _{RM}	5	V
Forward Current	I _F	30	mA
Junction Temperature	TJ	125	°C
Storage Temperature Range	T _{stg}	- 55 to + 125	°C

Electrical Characteristics at T_a = 25 °C

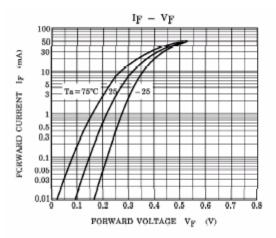
Parameter	Symbol	Min.	Тур.	Max.	Unit
Forward Current at $V_F = 0.5 V$	I _F	30	-	-	mA
Reverse Current at $V_R = 0.5 V$	I _R	-	-	25	μA
Total Capacitance at $V_R = 0.2 V$, f = 1 MHz	CT	-	0.6	-	pF

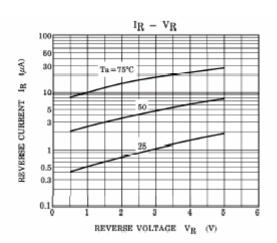


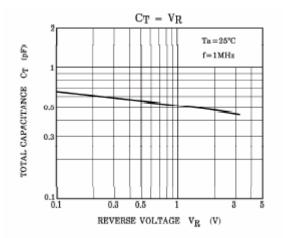




Dated : 01/09/2006











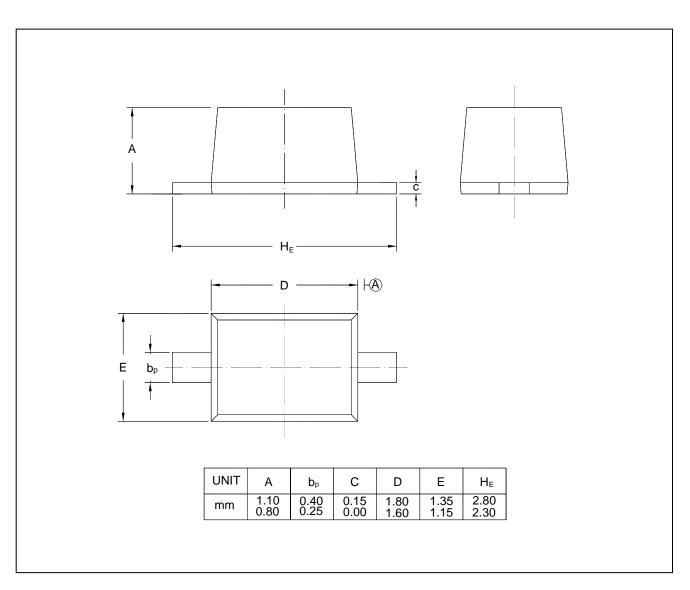


Dated : 01/09/2006

PACKAGE OUTLINE

Plastic surface mounted package; 2 leads

SOD-323





SEMTECH ELECTRONICS LTD. (Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



Dated : 01/09/2006